



**FUKUCOM COMPANY LTD.**

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

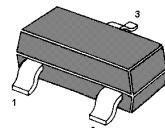
TEL: 852-2790 0314 FAX: 852-2790 0206

## MMBTSC1815

### NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into four groups O, Y, G and L, according to its DC current gain. As complementary type the PNP transistor MMBTSA1015 is recommended.



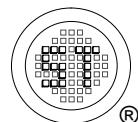
1. Base 2. Emitter 3. Collector  
SOT-23 Plastic Package

#### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter                 | Symbol    | Value         | Unit             |
|---------------------------|-----------|---------------|------------------|
| Collector Base Voltage    | $V_{CBO}$ | 60            | V                |
| Collector Emitter Voltage | $V_{CEO}$ | 50            | V                |
| Emitter Base Voltage      | $V_{EBO}$ | 5             | V                |
| Collector Current         | $I_C$     | 150           | mA               |
| Base Current              | $I_B$     | 50            | mA               |
| Power Dissipation         | $P_{tot}$ | 200           | mW               |
| Junction Temperature      | $T_j$     | 150           | $^\circ\text{C}$ |
| Storage Temperature Range | $T_{stg}$ | - 55 to + 150 | $^\circ\text{C}$ |

#### Characteristics at $T_{amb}=25^\circ\text{C}$

| Parameter   | Symbol                      | Min.     | Max. | Unit |
|---|-----------------------------|----------|------|------|
| DC Current Gain<br>at $V_{CE} = 6 \text{ V}$ , $I_C = 2 \text{ mA}$                       | $\text{Current Gain Group}$ |          |      |      |
|   | O                           | $h_{FE}$ | 70   | 140  |
|   | Y                           | $h_{FE}$ | 120  | 240  |
|   | G                           | $h_{FE}$ | 200  | 400  |
| at $V_{CE} = 6 \text{ V}$ , $I_C = 150 \text{ mA}$  | L                           | $h_{FE}$ | 350  | 700  |
|   |                             | $h_{FE}$ | 25   | -    |
| Collector Base Cutoff Current<br>at $V_{CB} = 60 \text{ V}$                               | $I_{CBO}$                   | -        | 100  | nA   |
| Emitter Base Cutoff Current<br>at $V_{EB} = 5 \text{ V}$                                  | $I_{EBO}$                   | -        | 100  | nA   |
| Collector Emitter Saturation Voltage<br>at $I_C = 100 \text{ mA}$ , $I_B = 10 \text{ mA}$ | $V_{CE(sat)}$               | -        | 0.25 | V    |
| Base Emitter Saturation Voltage<br>at $I_C = 100 \text{ mA}$ , $I_B = 10 \text{ mA}$      | $V_{BE(sat)}$               | -        | 1    | V    |
| Gain Bandwidth Product<br>at $V_{CE} = 10 \text{ V}$ , $I_C = 1 \text{ mA}$               | $f_T$                       | 80       | -    | MHz  |
| Output Capacitance<br>at $V_{CB} = 10 \text{ V}$ , $f = 1 \text{ MHz}$                    | $C_{ob}$                    | -        | 3    | pF   |





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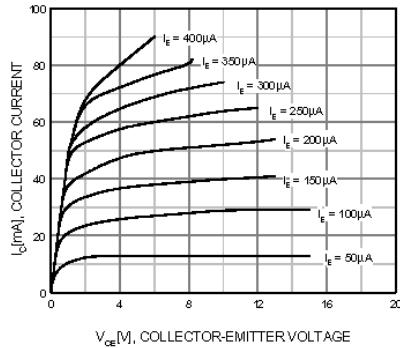


Figure 1. Static Characteristic

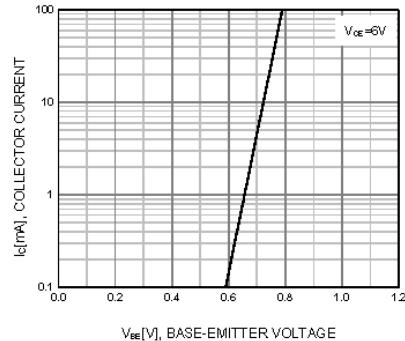


Figure 2. Transfer Characteristic

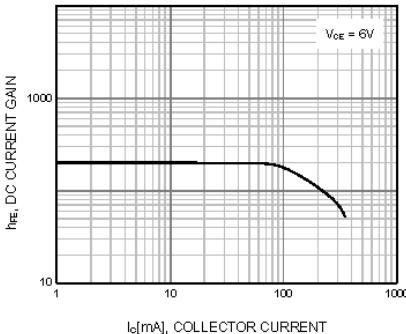


Figure 3. DC current Gain

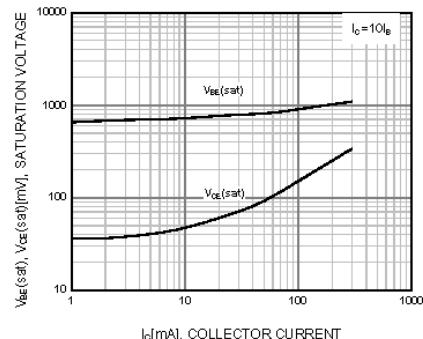


Figure 4. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

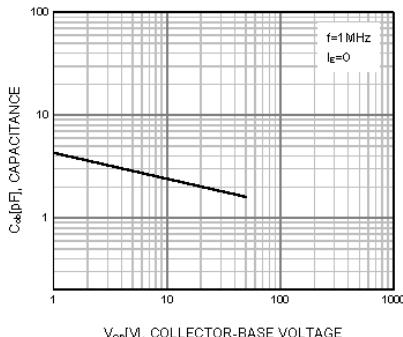


Figure 5. Output Capacitance

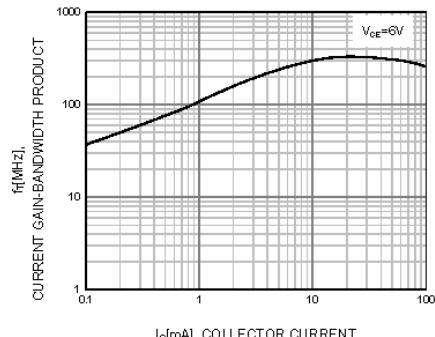


Figure 6. Current Gain Bandwidth Product

